

NTGS3443T1

Power MOSFET 2 Amps, 20 Volts P-Channel TSOP-6

Features

- Ultra Low $R_{DS(on)}$
- Higher Efficiency Extending Battery Life
- Miniature TSOP6 Surface Mount Package
- Pb-Free Package May be Available. The G-Suffix Denotes a Pb-Free Lead Finish

Applications

- Power Management in Portable and Battery-Powered Products, i.e.: Cellular and Cordless Telephones, and PCMCIA Cards

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Rating	Symbol	Value	Unit
Drain-to-Source Voltage	V_{DS}	-20	Volts
Gate-to-Source Voltage – Continuous	V_{GS}	± 12	Volts
Thermal Resistance Junction-to-Ambient (Note 1)	$R_{\theta JA}$	244	$^\circ\text{C/W}$
Total Power Dissipation @ $T_A = 25^\circ\text{C}$	P_d	0.5	Watts
Drain Current – Continuous @ $T_A = 25^\circ\text{C}$	I_D	-2.2	Amps
– Pulsed Drain Current ($T_p < 10 \mu\text{s}$)	I_{DM}	-10	Amps
Thermal Resistance Junction-to-Ambient (Note 2)	$R_{\theta JA}$	128	$^\circ\text{C/W}$
Total Power Dissipation @ $T_A = 25^\circ\text{C}$	P_d	1.0	Watts
Drain Current – Continuous @ $T_A = 25^\circ\text{C}$	I_D	-3.1	Amps
– Pulsed Drain Current ($T_p < 10 \mu\text{s}$)	I_{DM}	-14	Amps
Thermal Resistance Junction-to-Ambient (Note 3)	$R_{\theta JA}$	62.5	$^\circ\text{C/W}$
Total Power Dissipation @ $T_A = 25^\circ\text{C}$	P_d	2.0	Watts
Drain Current – Continuous @ $T_A = 25^\circ\text{C}$	I_D	-4.4	Amps
– Pulsed Drain Current ($T_p < 10 \mu\text{s}$)	I_{DM}	-20	Amps
Operating and Storage Temperature Range	T_J, T_{stg}	-55 to 150	$^\circ\text{C}$
Maximum Lead Temperature for Soldering Purposes for 10 Seconds	T_L	260	$^\circ\text{C}$

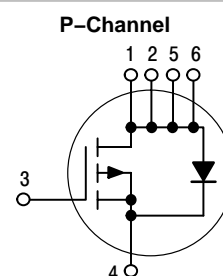
1. Minimum FR-4 or G-10PCB, operating to steady state.
2. Mounted onto a 2 in square FR-4 board (1" sq. 2 oz. cu. 0.06" thick single sided), operating to steady state.
3. Mounted onto a 2 in square FR-4 board (1" sq. 2 oz. cu. 0.06" thick single sided), $t < 5.0$ seconds.



ON Semiconductor®

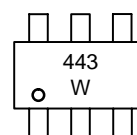
<http://onsemi.com>

2 AMPERES
20 VOLTS
 $R_{DS(on)} = 65 \text{ m}\Omega$



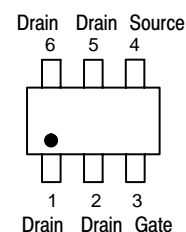
TSOP-6
CASE 318G
Style 1

MARKING DIAGRAM



443 = Device Code
W = Work Week

PIN ASSIGNMENT



ORDERING INFORMATION

Device	Package	Shipping†
NTGS3443T1	TSOP-6	3000 Tape & Reel
NTGS3443T1G	TSOP-6	3000 Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

NTGS3443T1

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted) (Notes 4 & 5)

Characteristic	Symbol	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain-Source Breakdown Voltage (V _{GS} = 0 Vdc, I _D = -10 μA)	V _{(BR)DSS}	-20	-	-	Vdc
Zero Gate Voltage Drain Current (V _{GS} = 0 Vdc, V _{DS} = -20 Vdc, T _J = 25°C) (V _{GS} = 0 Vdc, V _{DS} = -20 Vdc, T _J = 70°C)	I _{DSS}	-	-	-1.0 -5.0	μAdc
Gate-Body Leakage Current (V _{GS} = -12 Vdc, V _{DS} = 0 Vdc)	I _{GSS}	-	-	-100	nAdc
Gate-Body Leakage Current (V _{GS} = +12 Vdc, V _{DS} = 0 Vdc)	I _{GSS}	-	-	100	nAdc

ON CHARACTERISTICS

Gate Threshold Voltage (V _{DS} = V _{GS} , I _D = -250 μAdc)	V _{GS(th)}	-0.60	-0.95	-1.50	Vdc
Static Drain-Source On-State Resistance (V _{GS} = -4.5 Vdc, I _D = -4.4 Adc) (V _{GS} = -2.7 Vdc, I _D = -3.7 Adc) (V _{GS} = -2.5 Vdc, I _D = -3.5 Adc)	R _{DS(on)}	-	0.058 0.082 0.092	0.065 0.090 0.100	Ω
Forward Transconductance (V _{DS} = -10 Vdc, I _D = -4.4 Adc)	g _{FS}	-	8.8	-	mhos

DYNAMIC CHARACTERISTICS

Input Capacitance	(V _{DS} = -5.0 Vdc, V _{GS} = 0 Vdc, f = 1.0 MHz)	C _{iss}	-	565	-	pF
Output Capacitance		C _{oss}	-	320	-	pF
Reverse Transfer Capacitance		C _{rss}	-	120	-	pF

SWITCHING CHARACTERISTICS

Turn-On Delay Time	(V _{DD} = -20 Vdc, I _D = -1.0 Adc, V _{GS} = -4.5 Vdc, R _g = 6.0 Ω)	t _{d(on)}	-	10	25	ns
Rise Time		t _r	-	18	45	ns
Turn-Off Delay Time		t _{d(off)}	-	30	50	ns
Fall Time		t _f	-	31	50	ns
Total Gate Charge	(V _{DS} = -10 Vdc, V _{GS} = -4.5 Vdc, I _D = -4.4 Adc)	Q _{tot}	-	7.5	15	nC
Gate-Source Charge		Q _{gs}	-	1.4	-	nC
Gate-Drain Charge		Q _{gd}	-	2.9	-	nC

BODY-DRAIN DIODE RATINGS

Diode Forward On-Voltage	(I _S = -1.7 Adc, V _{GS} = 0 Vdc)	V _{SD}	-	-0.83	-1.2	Vdc
Reverse Recovery Time	(I _S = -1.7 Adc, dI _S /dt = 100 A/μs)	t _{rr}	-	30	-	ns

4. Indicates Pulse Test: P.W. = 300 μsec max, Duty Cycle = 2%.
5. Handling precautions to protect against electrostatic discharge is mandatory.

TYPICAL ELECTRICAL CHARACTERISTICS

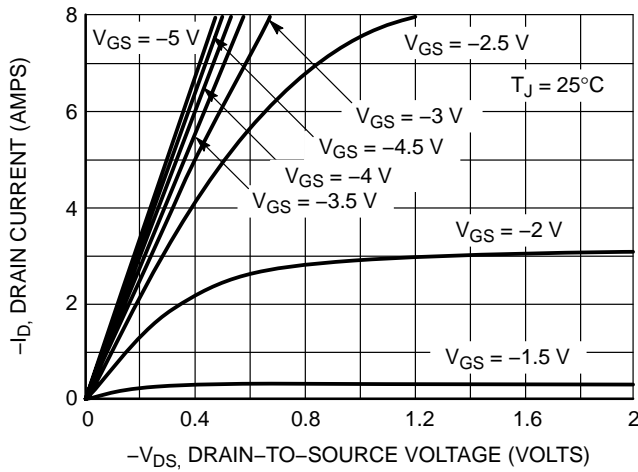


Figure 1. On-Region Characteristics

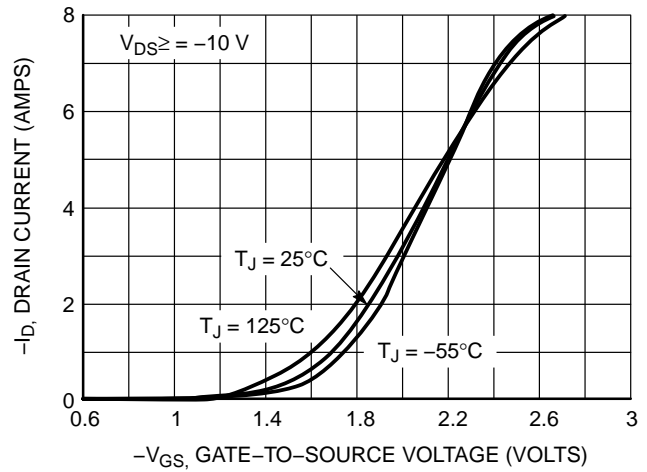


Figure 2. Transfer Characteristics

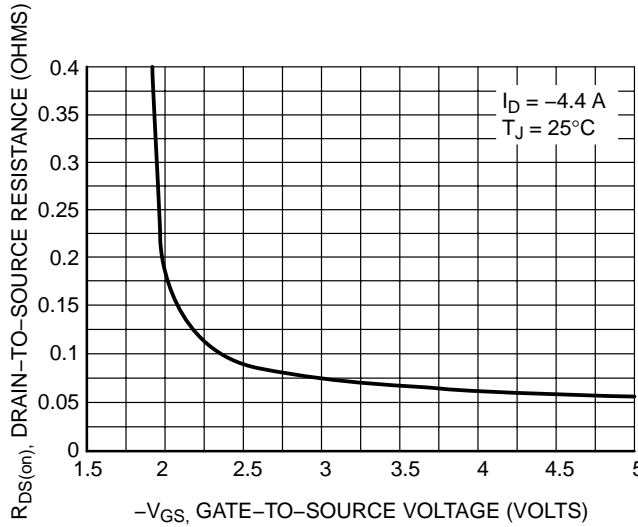


Figure 3. On-Resistance vs. Gate-to-Source Voltage

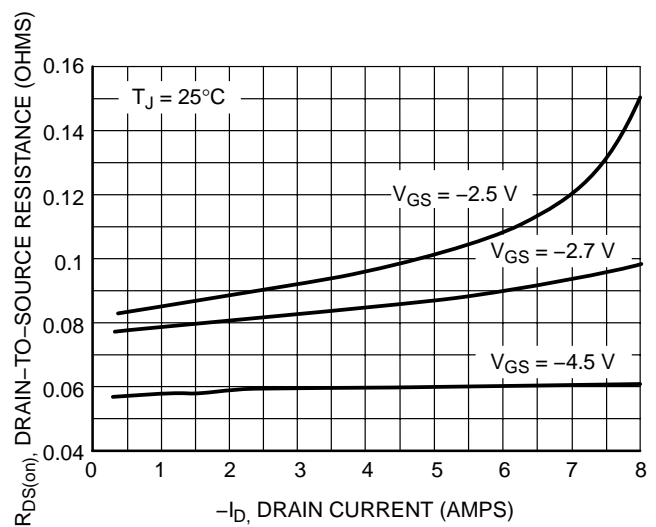


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

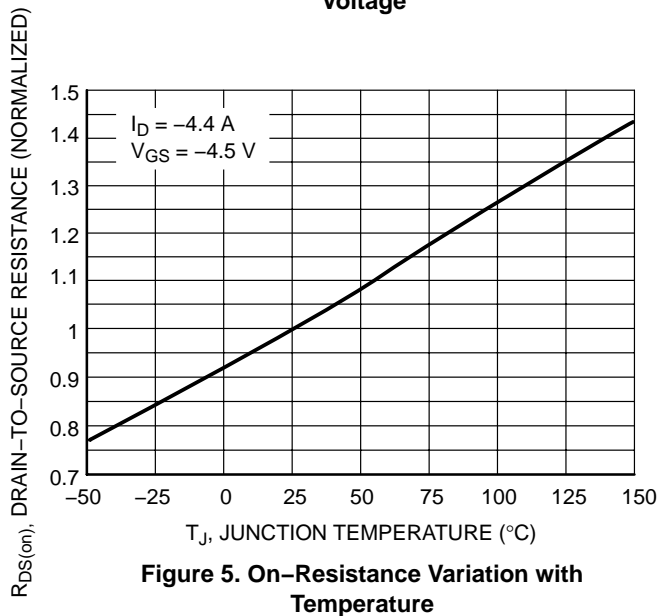


Figure 5. On-Resistance Variation with Temperature

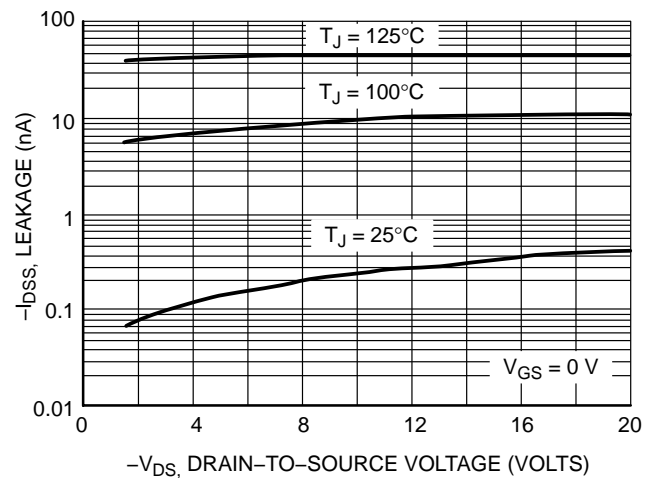


Figure 6. Drain-to-Source Leakage Current vs. Voltage

TYPICAL ELECTRICAL CHARACTERISTICS

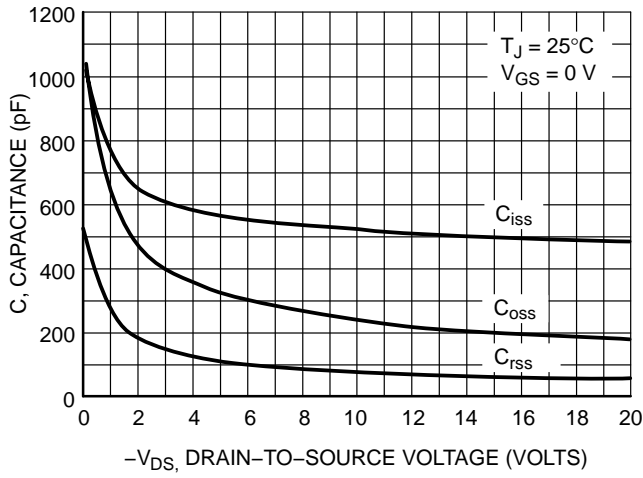


Figure 7. Capacitance Variation

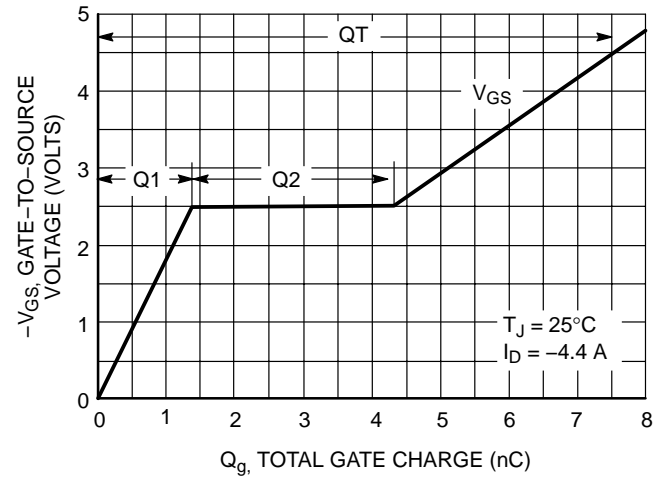


Figure 8. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

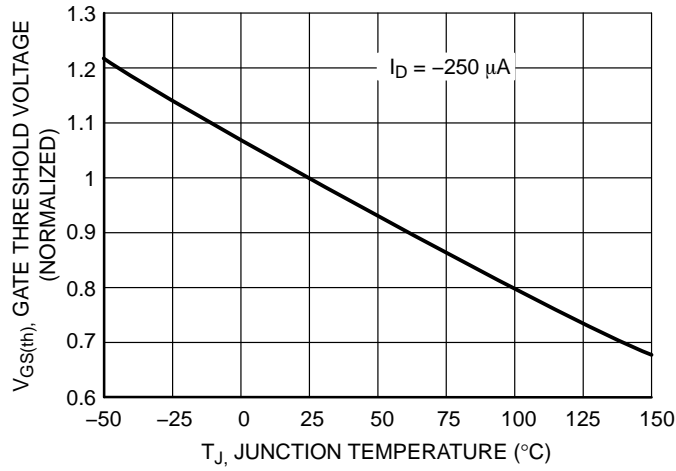


Figure 9. Gate Threshold Voltage Variation with Temperature

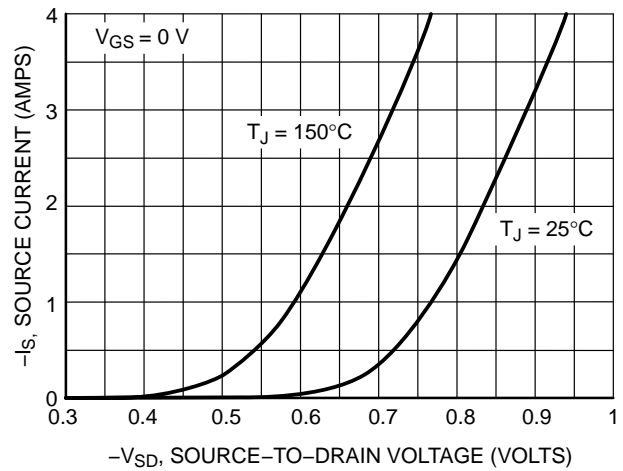


Figure 10. Diode Forward Voltage vs. Current

NTGS3443T1

TYPICAL ELECTRICAL CHARACTERISTICS

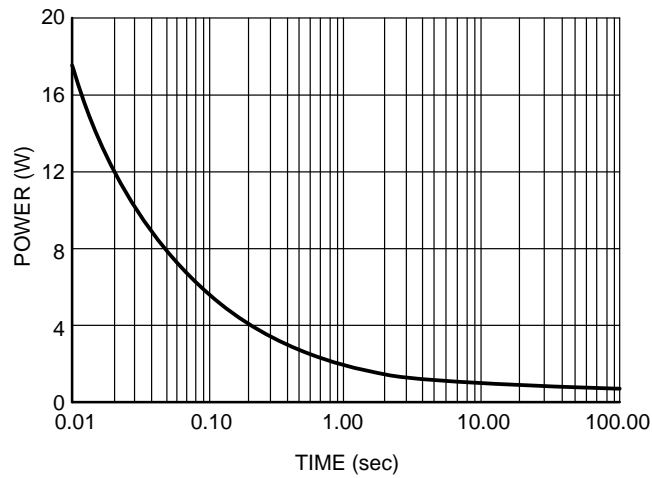


Figure 11. Single Pulse Power

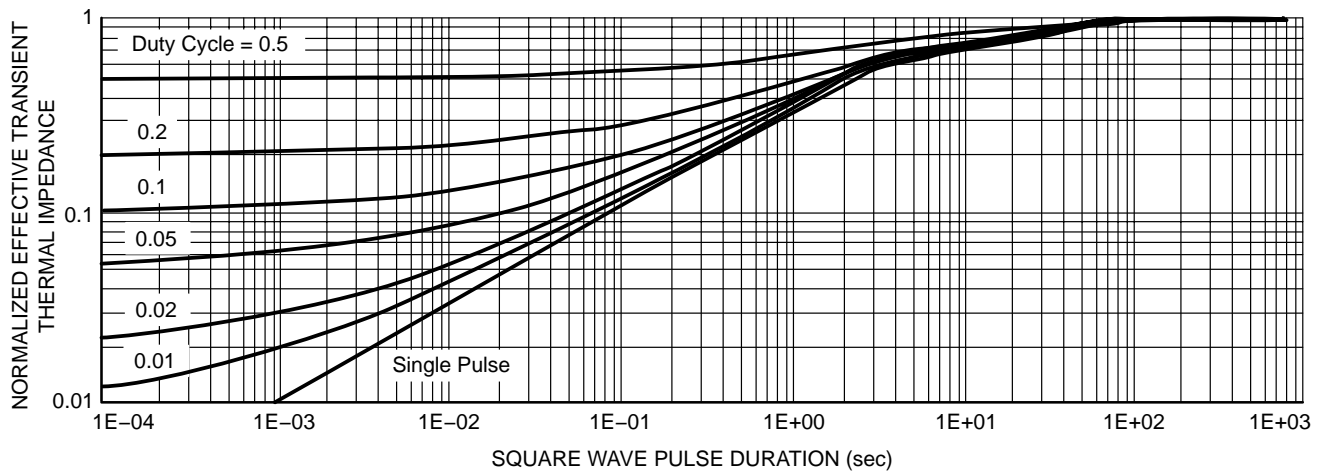
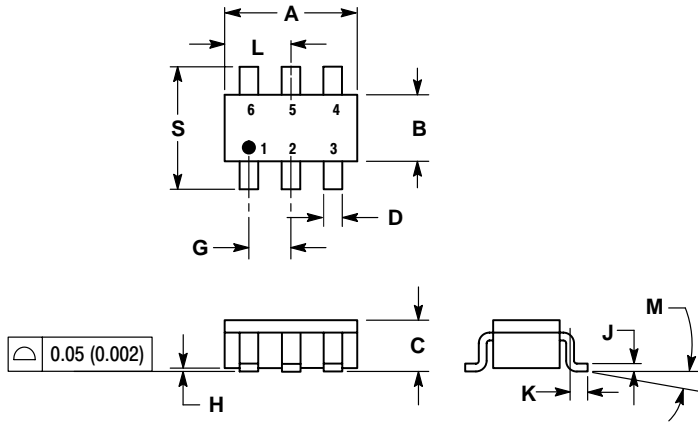


Figure 12. Normalized Thermal Transient Impedance, Junction-to-Ambient

NTGS3443T1

PACKAGE DIMENSIONS

TSOP-6 CASE 318G-02 ISSUE K



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	2.90	3.10	0.1142	0.1220
B	1.30	1.70	0.0512	0.0669
C	0.90	1.10	0.0354	0.0433
D	0.25	0.50	0.0098	0.0197
G	0.85	1.05	0.0335	0.0413
H	0.013	0.100	0.0005	0.0040
J	0.10	0.26	0.0040	0.0102
K	0.20	0.60	0.0079	0.0236
L	1.25	1.55	0.0493	0.0610
M	0	10	0	10
S	2.50	3.00	0.0985	0.1181

STYLE 1:

- PIN 1: DRAIN
- DRAIN
- GATE
- SOURCE
- DRAIN
- DRAIN

SOLDERING FOOTPRINT*

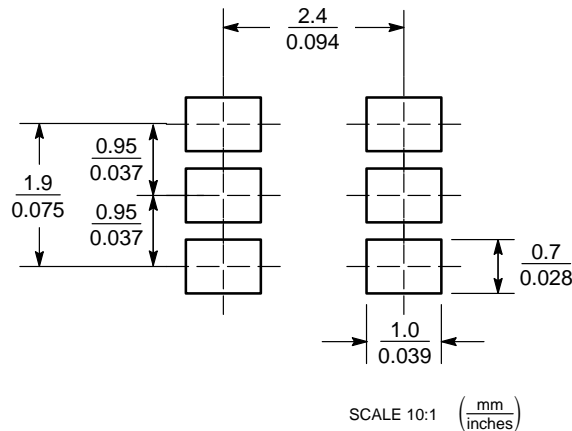


Figure 13. TSOP-6

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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